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The Field-Tuned Superconductor-Insulator Transition with and without Current Bias

E. Bielejec and Wenhao Wu
Department of Physics and Astronomy, University of Rochester, Rochester, New York 14627
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The magnetic-field-tuned superconductor-insulator transition has been studied in ultrathin Beryllium films quench-condensed near 20 K. In the zero-current limit, a finite-size scaling analysis yields the scaling exponent product $\nu z = 1.35 \pm 0.10$ and a critical sheet resistance R_c of about $1.2R_Q$, with $R_Q = h/4e^2$. However, in the presence of dc bias currents that are smaller than the zero-field critical currents, νz becomes 0.75 ± 0.10. This new set of exponents suggests that the field-tuned transitions with and without dc bias currents belong to different universality classes.

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The superconductor-insulator (SI) transition in ultrathin films is believed to be a continuous quantum phase transition [1] occurring at $T = 0$ as the quantum ground state of the system is tuned by varying disorder, film thickness, magnetic field, or carrier concentration through a critical value. Models of the SI transition can be grouped into two categories: ones that rely on fluctuations in the phase [2–5] and others that rely on fluctuations in the amplitude [6] of the order parameter to drive the transition. For models in the first category, Cooper pairs are assumed to be present on the superconducting side as well as on the insulating side of the transition. Based on this "dirty-boson" model, Fisher *et al.* [3,4] have proposed a phase diagram for a two-dimensional system as a function of disorder and magnetic field, with the transition being described in terms of interacting bosons (the Cooper pairs) in the presence of disorder. In the vicinity of the quantum critical point, the resistance is predicted to obey the scaling law [3,4]:

$$R(\delta, T) \propto R_c f(\delta t), \tag{1}$$

where $t(T) = T^{-1/\nu z}$, and δ is the deviation of a tuning parameter from its critical value. For field-tuned transitions, $\delta = |B - B_c|$ with B and B_c being the applied magnetic field and the critical field, respectively. The critical resistance R_c is predicted to have a universal value of $R_Q = h/4e^2 \approx 6.5$ kΩ/□. Scaling arguments set a lower bound on the correlation length exponent $\nu \geq 1$ [1] and give the value of the dynamical critical exponent $z = 1$ [3,4]. Experimentally, critical exponents consistent with these predictions have been found in scaling analyses of the field-tuned transitions in InO_x [7] and MoGe [8]. However, the predicted universal critical resistance is not observed in these experiments.

In this Letter, we report studies of the field-tuned SI transition in ultrathin Be films quench-condensed near 20 K. We describe scaling analyses of the field-tuned transition based on the "dirty boson" model. We have found that, for measurements performed in the zero-current limit, the scaling exponent product $\nu z = 1.35 \pm 0.10$. This agrees well with results of the field-tuned transition in relatively thicker InO_x [7] and MoGe [8] films, but disagrees with a recent report [9,10] of $\nu z = 0.7$ for the field-tuned transition in ultrathin Bi/Ge films. For our Be films having a robust superconducting phase, R_c appears to be near $1.2R_Q$ in the field-tuned transition. This agrees well with results from the Bi/Ge films [9,10]. We have also carried out for the first time studies of the field-tuned transition in the presence of a dc bias current. The applied dc bias current should exert a force of $\mathbf{j} \times \mathbf{B}$ on the vortices in the direction perpendicular to both the applied magnetic field $\mathbf{B}$ and the current density $\mathbf{j}$. We have observed that the scaling exponent product νz becomes 0.75 ± 0.10 in the presence of dc bias currents, suggesting that the field-tuned transitions with and without dc bias current belong to different universality classes.

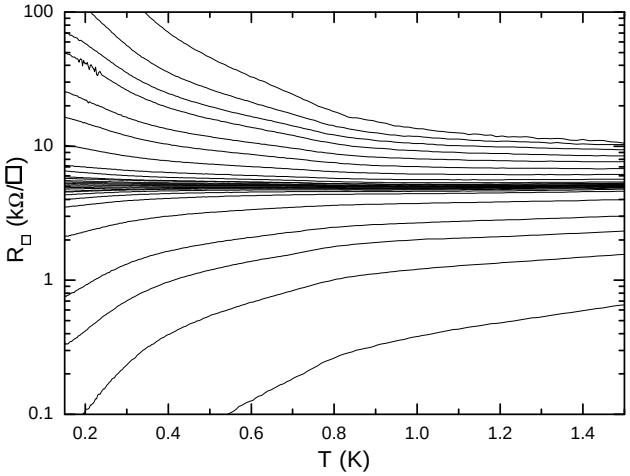

FIG. 1. Sheet resistance versus temperature measured on one marginally superconducting film at various magnetic field values. For curves from bottom to top, the field increased from 0.05 T to 2.25 T. The critical field was 0.66 T. In zero-field, $T_c \sim 2$ K.

In Fig. 1, we show, with zero bias current, the temperature dependence of the sheet resistance, $R_\square$, measured

at various field values for one of our Be films with the magnetic field applied perpendicular to the plane of the film. These Be films were quench-condensed onto bare glass substrates which were held near 20 K during evaporations, under UHV conditions inside a dilution refrigerator. This *in situ* progressive evaporation setup allowed for systematic studies of the SI transition as film thickness was varied. We deposited each set of films in fine steps. We carefully monitored $R_\Box$ during each evaporation step until a desirable value of $R_\Box$ was reached. The films were very close to 10 Å in thickness, however, our quartz thickness monitor was not sensitive enough to pick up the small thickness increments after each step. Film resistance was measured in a standard four-terminal geometry using a PAR-124A lock-in amplifier operating at 27 Hz. The ac probe current was fixed at 1 nA. At the finite measuring temperatures in the vicinity of the field-tuned transition, the *I-V* characteristics in this low-current regime were linear. More details regarding these Be films have been published elsewhere [11]. Quench-condensed Be films are chosen for this study because such films were found to be nearly amorphous [11]. These Be films undergo a transition from insulating to superconducting [11] when the normal state sheet resistance, R_N, is reduced below ~ 10 kΩ/□ with increasing film thickness. We have now studied the field-tuned SI transition in several films of R_N between 5.6 and 12 kΩ/□. The superconducting transition temperature, T_c, of these films varied between 0.5 to 4 K in zero-field.

The film in Fig. 1, with $R_N = 10.7$ kΩ/□ at 15 K, is considered marginally superconducting, as we will discuss later. With increasing field, corresponding to curves from the bottom to the top in Fig. 1, this film was driven from superconducting to insulating, with a rather flat $R_\Box$ vs. T curve at a critical field of $B_c = 0.66$ T. The main part of Fig. 2(a) shows $R_\Box$ vs. B at various temperatures for the same film as shown in Fig. 1. In the vicinity of a quantum critical point, the resistance of a two-dimensional system is predicted to obey the scaling law in Eq. (1). Determining the critical exponents involves plotting the $R_\Box$ vs. B data at various temperatures according to the scaling law. The good crossing point, over one decade in temperature, in the $R_\Box$ vs. B plot in the main part of Fig. 2(a) identifies $B_c = 0.66$ T and $R_c = 4.4$ kΩ/□ for this film. We have used two methods to determine the scaling exponent νz. First, we can find νz by evaluating the derivative of the $R_\Box$ vs. B curve at the critical field. In this case, we have the following scaling equation:

$$\frac{\partial R}{\partial B}|_{B_c} \propto R_c T^{-1/\nu z} f'(0). \qquad (2)$$

A plot of $\frac{\partial R}{\partial B}|_{B_c}$ vs. T^{-1} on a log-log scale, shown in the inset to Fig. 2(a), yields a straight line with a slope equal to $1/\nu z$, from which we determine $\nu z = 1.36 \pm 0.10$. Alternatively, we can plot R/R_c vs. $|B - B_c|t$ and treat $t(T)$ as an unknown variable. The values of

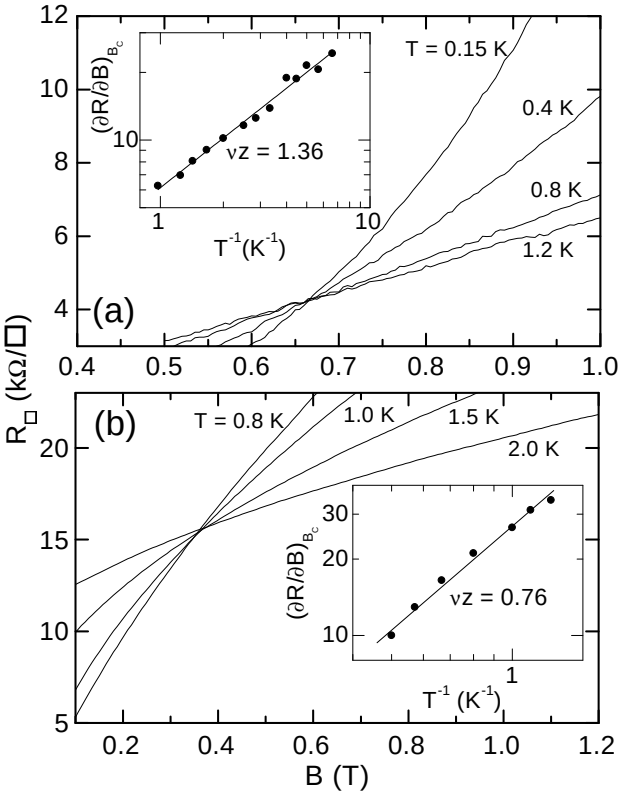

FIG. 2. Main figures show sheet resistance vs. field at a number of temperatures as labeled in the figures, with $I_{bias} = 0$ in (a) and $I_{bias} = 2.5$ μA in (b). The crossing points identify the critical fields and critical resistances. Insets show the power-law relations between $\frac{\partial R}{\partial B}|_{B_c}$ and T^{-1} for the corresponding I_{bias} values, which determine the values of νz.

$t(T)$ at various temperatures are determined by obtaining the best collapse of the data. Following this procedure presented in recent papers [9,10] by N. Markovic *et al.*, we obtain the temperature dependence of $t(T)$ which we plot on a log-log scale in the inset to Fig. 3(a). The collapse of the data is shown in the main part of Fig. 3(a) in a R/R_c vs. $|B - B_c|t$ plot. Figure 3(a) shows good collapse of the data over three orders of magnitude in $|B - B_c|t$ and two orders of magnitude in R/R_c. The straight line in the inset to Fig. 3(a) shows a power-law fit, as expected by the scaling function, Eq. (1). The slope of the line in the inset gives -1/νz, from which we find $\nu z = 1.34 \pm 0.10$. The exponents obtained from the above two methods agree with each other, showing the consistency of the scaling analysis. The scaling exponents obtained in our Be films in the zero-bias limit appear to be in very good agreement with the predictions of theories based on the "dirty boson" model [3,4]. Our result is also in very good agreement with renormalization group theories [12,13] and Monte Carlo [5] simulations.

Another important prediction of the bosonic model is the universal critical resistance $R_c = R_Q = h/4e^2 \approx 6.5$ kΩ/□ at the quantum critical point. This remains a controversial issue since only in the Bi/Ge sys-

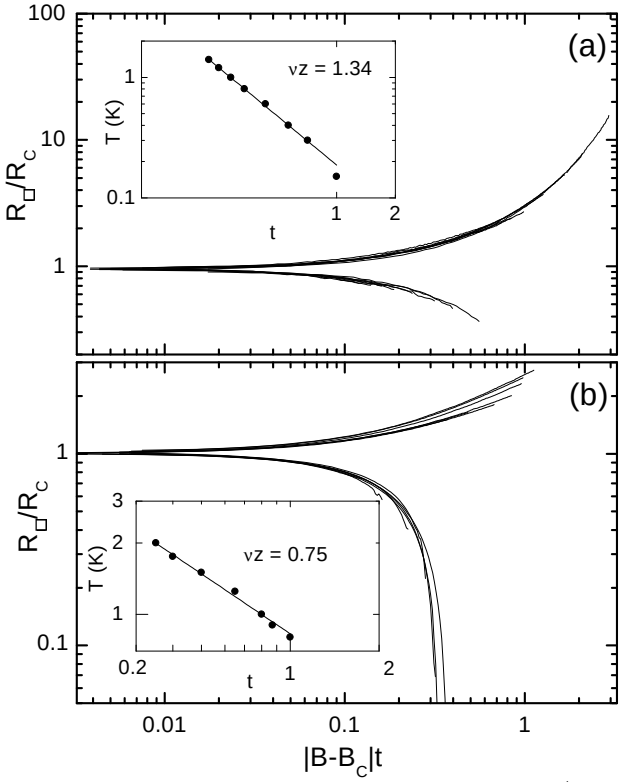

FIG. 3. Main figures show the scaling plots of R/R_c vs. $|B - B_c|t$, with $I_{bias} = 0$ in (a) and $I_{bias} = 2.5$ μA in (b). Insets show the power-law relations between the parameter t and the temperature, which determine the values of νz.

tem [9,10] has a critical sheet resistance close to the predicted value of R_Q been observed. In fact, careful investigations in the Bi/Ge system have revealed that R_c is $1.1R_Q$ to $1.2R_Q$ and decreases in a narrow range as R_N is reduced with increasing film thickness. It was suggested [9] that the slightly larger R_c than R_Q was consistent with calculations in two-dimensions for a bosonic model including Coulomb interactions [14], which predicted $R_c \sim 1.4R_Q$, as well as Monte Carlo simulations in the (2+1)-dimensional XY model without disorder [15], which found $R_c = 1.2R_Q$. The small variation of R_c with R_N could be explained [10] as a finite-temperature effect, since strictly speaking the critical resistance is predicted to be universal only at $T = 0$. In other systems, such as MoGe [8] films, R_c varies in a much wider range among films of varying R_N. In order to explain the low R_c of their MoGe films, Yazdani and Kapitulnik proposed [8] a two-channel model in which the conductance due to normal electrons add to the conductance due to the Cooper pairs. If the unpaired electrons are localized, this model collapses to a single channel bosonic model with $R_c = R_Q$. Otherwise, unpaired electrons add to the conduction at the transition. It has been noted [10] that the resulting film resistance can be either larger or smaller than R_Q since the magnetoresistance contribution [16] from the unpaired electrons can be either positive, if the

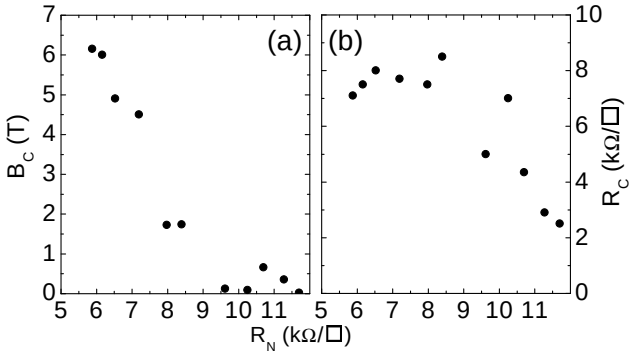

FIG. 4. Figures show (a) the critical field, B_c, and (b) the critical resistance, R_c, as functions of the normal-state sheet resistance, R_N, measured at 15 K.

spin-orbit coupling is strong, or negative, if the spin-orbit coupling is very weak.

Our Be films showed a zero-field SI transition as R_N was reduced below ~ 10 k$\Omega/\Box$ with increasing film thickness [11]. Films of R_N near 11 k$\Omega/\Box$ are considered marginally superconducting since they have near-zero critical field values. Further increasing film thickness, the critical field, B_c, increases with decreasing R_N, as shown in Fig. 4(a). In Fig. 4(b), we plot how R_c in the field-tuned transition varies with R_N. For marginally superconducting films of R_N between 9 to 12 k$\Omega/\Box$, R_c was significantly smaller than R_Q. Nevertheless, we see clearly by comparing Fig. 4(a) with Fig. 4(b) that, as R_N was reduced by increasing film thickness, films with robust critical field values have a R_c of $7.1 \sim 8.0$ k$\Omega/\Box$ in the field-tuned SI transition, which is about $1.2R_Q$. This result is in excellent agreement with results from the Bi/Ge system [10]. However, our results disagree with the suggestion [10] that the magnetoresistance of the unpaired electrons caused the discrepancy between R_c and R_Q. Since Be has the weakest spin-orbit coupling among metals, the magnetoresistance should be negative, leading to $R_c < R_Q$ following the two-channel model. We note that we have shown in Fig. 1, Fig. 2(a), and Fig. 3(a) data measured on a marginally superconducting film of $R_N = 10.7$ k$\Omega/\Box$ at 15 K. Although the critical resistance of this film, $R_c \sim 4.4$ k$\Omega/\Box$, is significantly smaller than R_Q, we have found that, for all the marginally and robust superconducting films of R_N ranging from 5.6 to 12 k$\Omega/\Box$, the critical exponents are the same with $\nu z = 1.35 \pm 0.10$ in the zero-current limit.

Below, we describe results of the field-tuned SI transition in the presence of a dc bias current, I_{bias}. For such studies, I_{bias} was varied between 125 nA and 2.5 μA and kept below the zero-field critical current (~ 15 μA). At each fixed I_{bias}, we used a magnetic field to tune a film from superconducting to insulating. We believe that joule heating was insignificant in our experiments based on the following arguments. First, we have performed extensive I-V measurements over the entire tem-

perature and magnetic field range of our experiments, with the time span for the I-V sweeps ranging from ten minutes to one hour. The I-V curves were completely reproducible without any observable hysteresis and independent of the sweep rate. Secondly, we can estimate the temperature increase, ΔT, on the Be films due to joule heating. The thin Be films were deposited on glass microslide substrates of thickness 0.23 mm, which was attached to a copper sample holder by a very thin layer of grease. The glass substrate was the dominant source of heat resistance, with a thermal conductivity of ~ 0.0003 W/Km at 100 mK [17]. For a typical film square of size 3×3 mm^2 and resistance 10 kΩ, joule heating for $I_{bias} =$ 125 nA is about 0.15 nW, resulting in $\Delta T \sim 0.012$ mK at 100 mK. For $I_{bias} = 2.5$ μA, $\Delta T \sim 5.0$ mK at 100 mK. We note that the heating power at 2.5 μA was 400 times larger than the heating power at 125 nA. If joule heating were significant, the data obtained with $I_{bias} =$ 2.5 μA should show a flattening of the data in the low temperature region when compared to the data obtained with $I_{bias} = 125$ nA. The fact that the scaling results at 125 nA and 2.5 μA agree well suggests that heating was insignificant. This also argues against the existence of significant electron heating decoupled from the lattice.

We plot in Fig. 2(b) and Fig. 3(b), for $I_{bias} = 2.5$ μA, the results of scaling analyses based on the two previously described methods. In Table I, we list the parameters from scaling analyses of the field-tuned transition at various I_{bias}. Results from the data collapsing method are presented for I_{bias} values of 250 nA and 2.5 μA, for which the amount of data taken was adequate for such analyses. It appears that $\nu z \sim 0.75 \pm 0.10$, showing no systemic change with I_{bias} in the range we have studied. Nevertheless, it is significantly smaller than the νz found in the zero-current limit. We can only speculate that the bias current could lead to a symmetry-breaking, resulting in different critical behavior at the transition. We note that experiments need to be carried out in other systems in order to find out whether this result is universal. In addition, experiments at low I_{bias} values should be carried out to determine whether νz changes abruptly or gradually as I_{bias} is increased from zero. Such experiments can probe the threshold I_{bias} for the change in the scaling exponents, and have the potential of revealing whether the new scaling exponents are produced by certain nonlinear effects in the vortices under a bias current. On the other hand, we need to discuss other possible origins that might have led to the new scaling exponents. For example, transport in marginally superconducting films, or, in the presence of a dc bias, could be dominated by narrow superconducting filaments, leading to a change in the dimensionality of the system. While it is difficult to determine to what extent film inhomogeneity affects our experiments, we would like to comment on the critical currents measured in our films. For the film shown in Fig. 2(b) and Fig. 3(b), the critical current in zero field was about 1.5×10^{-5} A. This film was about 10 Å in thickness and 3 mm in width. Thus, the critical current density would be about 5×10^6 A/m^2 if the current were uniformly distributed in the bulk of the film. On the other hand, if we assume that the current runs through a few filaments of 100 Å in total width, the critical current density would be 1.5×10^{12}A/m^2. The critical currents of amorphous Be films have been measured by other groups, for example by Okamoto *et al.* [18]. Their Be films had a resistivity of 3.6×10^{-6} Ωm. This value gives rise to $R_\Box \sim 3.6$ k$\Omega/\Box$ for a film of thickness same as ours ($\approx$ 10 Å), meaning that their films were roughly 3 times less resistive than ours. They found that their films had critical current density of about 1×10^8 A/m^2. Compared to their critical current density, the assumption in our films of conduction dominated by a few narrow filaments leads to an unreasonably large critical current density. In addition, we can compare our marginally superconducting films with robust superconducting films which are unlikely to be dominated by narrow filaments. As we have discussed, with $I_{bias} = 0$, these two types of films showed identical scaling exponents νz. It is possible that film inhomogeneity has lead to a depressed R_c in marginally superconducting films, but has not changed the effective dimensionality of the system. Therefore, the change in the scaling exponents with a dc bias is unlikely due to a dimensional cross-over as a result of filamentary superconductivity.

TABLE I. Bias currents and derived parameters

I_{bias} (nA)	B_c (T)	R_c (k$\Omega/\Box$)	R_N (k$\Omega/\Box$)	νz *	νz †
125	0.33	15.5	9.36	0.81	–
250	0.35	16.1	9.36	0.76	0.73
1000	0.36	15.5	9.36	0.73	–
2500	0.38	15.0	9.36	0.77	0.75

*νz obtained by the $\frac{\partial R}{\partial B}|_{B_c}$ method

†νz obtained by the data collapse method

In conclusion, the scaling exponents found in our Be films in the zero-biased, field-tuned SI transition agree very well with results from InO_x [7] and MoGe [8] films, but disagrees with recent results [9,10] from quench-condensed Bi/Ge films. For Be films having a robust superconducting phase, the critical sheet resistance in the field-tuned SI transition was about $1.2R_Q$. Our field-tuned transition in the presence of a dc current reveals a set of new scaling exponents, suggesting that the field-tuned transitions with and without dc bias belong to different universality classes. We gratefully acknowledge S. Teitel and Y. Shapir for numerous useful discussions.

[1] S. L. Sondhi *et al.*, Rev. Mod. Phys. **69**, 315 (1997).
[2] M. P. A. Fisher *et al.*, Phys. Rev. B **40**, 546 (1989).
[3] M. P. A. Fisher, Phys. Rev. Lett. **65**, 923 (1990).
[4] M. P. A. Fisher, G. Grinstein, and S. M. Girvin, Phys. Rev. Lett. **64**, 587 (1990).
[5] M.-C. Cha *et al.*, Phys. Rev. B **44**, 6883 (1991)
[6] J. M. Valles, Jr., R. C. Dynes, and J. P. Garno, Phys. Rev. Lett. **69**, 3567 (1992); S-Y. Hsu, J. A. Chervenak, and J. M. Valles, Jr., *ibid.* **75**, 132 (1995).
[7] A. F. Hebard and M. A. Paalanen, Phys. Rev. Lett. **65**, 927 (1990); M. A. Paalanen, A. F. Hebard, and R.R. Ruel, *ibid* **69**, 1604 (1992).
[8] Ali Yazdani and Aharon Kapitulnik, Phys. Rev. Lett. **74**, 3037 (1995); D. Ephron, A. Yazdani, A. Kapitulnik, and M. R. Beasley, *ibid.* **76**, 1529 (1996).
[9] N. Markovic, C. Christiansen, and A. M. Goldman, Phys. Rev. Lett. **81**, 5217 (1998).
[10] N. Markovic *et al.*, Phys. rev. B **60**, 4320 (1999).
[11] E. Bielejec, J. Ruan, and Wenhao Wu, Phys. Rev. B **63**, 100502 (2001); E. Bielejec, J. Ruan, and Wenhao Wu, Phys. Rev. Lett. **87**, 036801 (2001).
[12] L. Zhang and M. Ma, Phys. Rev. B **45**, 4855 (1992).
[13] K. G. Singh and D. S. Rokhsar, Phys. Rev. B **46**, 3002 (1992).
[14] Igor F. Herbut, Phys. Rev. Lett. **81**, 3916 (1998).
[15] M. -C. Cha and S. M. Girvin, Phys. Rev. B **49**, 9794 (1994).
[16] G. Bergmann, Phys. Rep, **107**, 1 (1984).
[17] G. K. White, *Experimental Techniques in Low Temperature Physics*, 3rd ed., (Clarendon Press, Oxford, 1979), p. 320.
[18] M. Okamoto, K. Takei, and S. Kubo, J. Appl. Phys. **62**, 212 (1987)